

Supporting information

Supramolecular Interactions Using β -Cyclodextrin in Controlling Perovskite Solar Cell Performance

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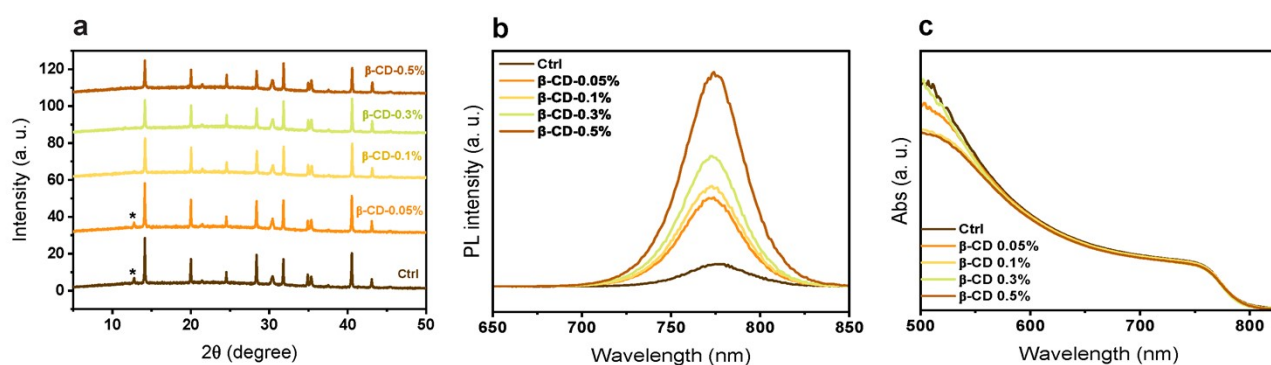


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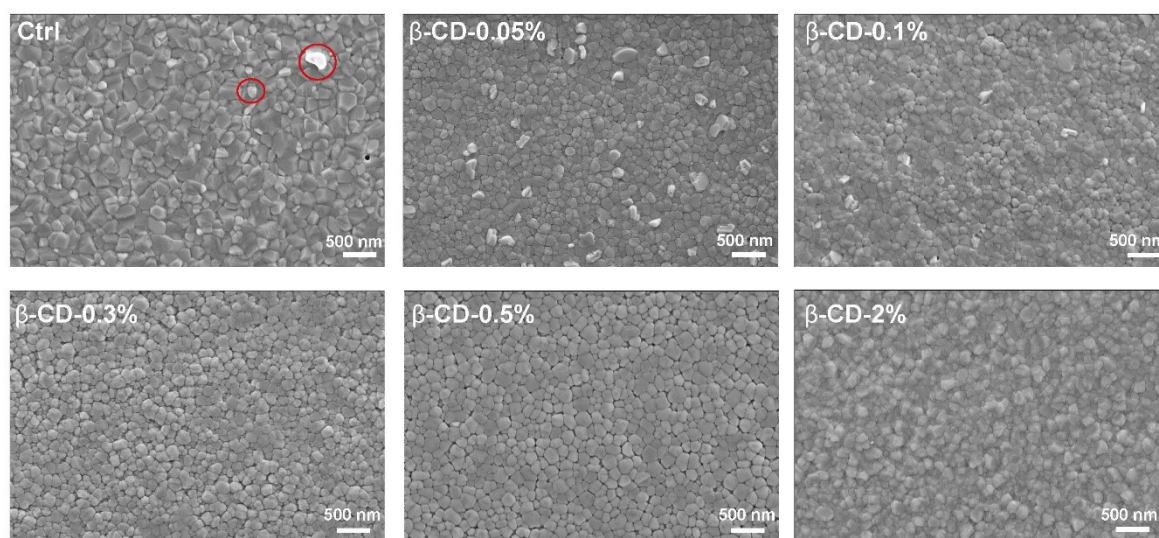


Figure S2. Top view SEM images of control (ctrl) and treated perovskite films with varying concentrations of β -CD. Red circles represent PbI_2 crystals.

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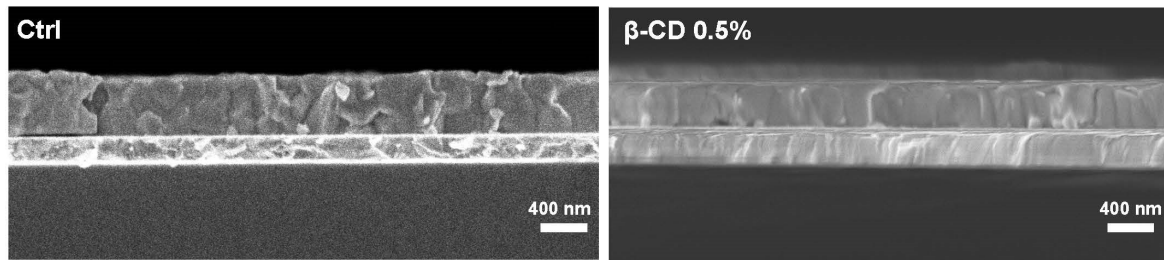


Figure S3. Cross section SEM images of control (left) and treated sample by 0.5% of β -CD (right).

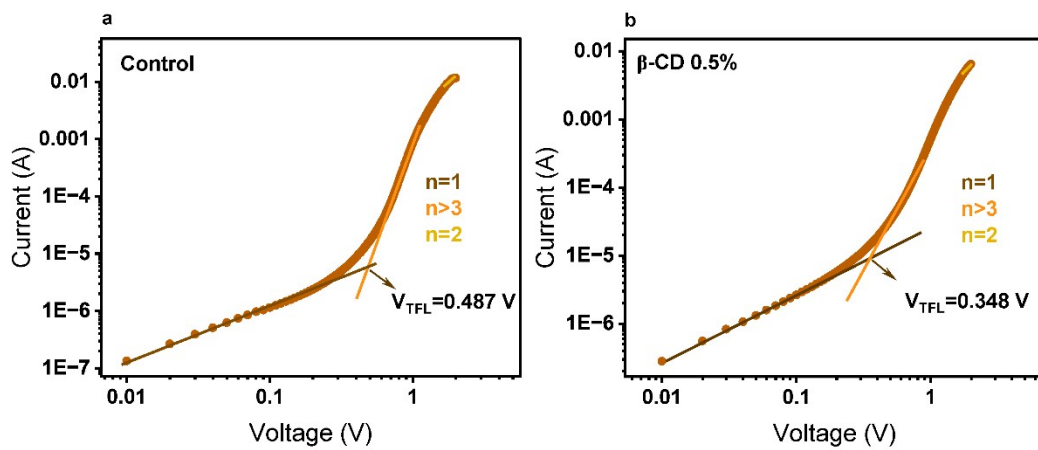


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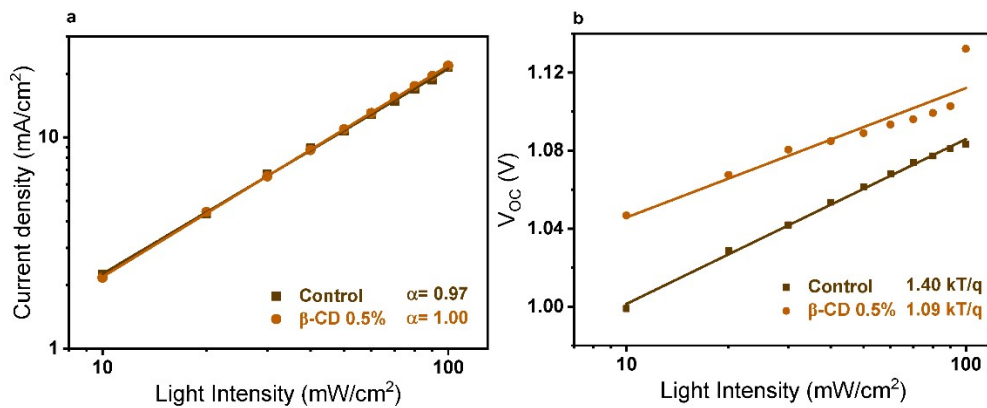


Figure S5. The dependence of a) J_{SC} and b) V_{OC} on the incident light intensity in case of (a) control and (b) treated sample by 0.5% of β -CD.

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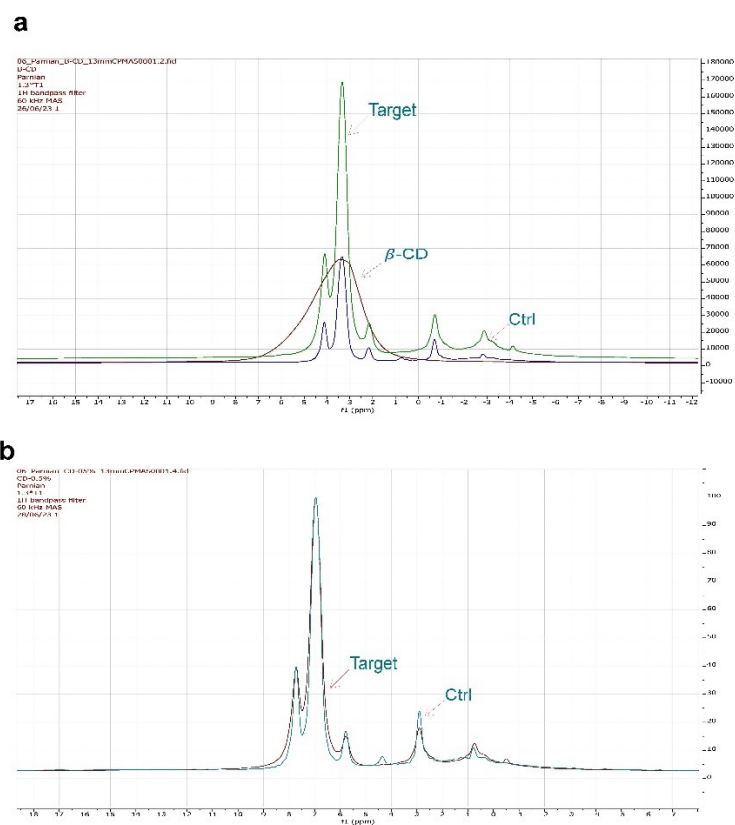


Figure S6. a) Solid-state NMR and b) normalized solid-state NMR of control, β -CD 0.5% treated perovskite and β -CD powders (Ctrl and target refer to pristine perovskite film and β -CD-treated perovskite film, respectively).

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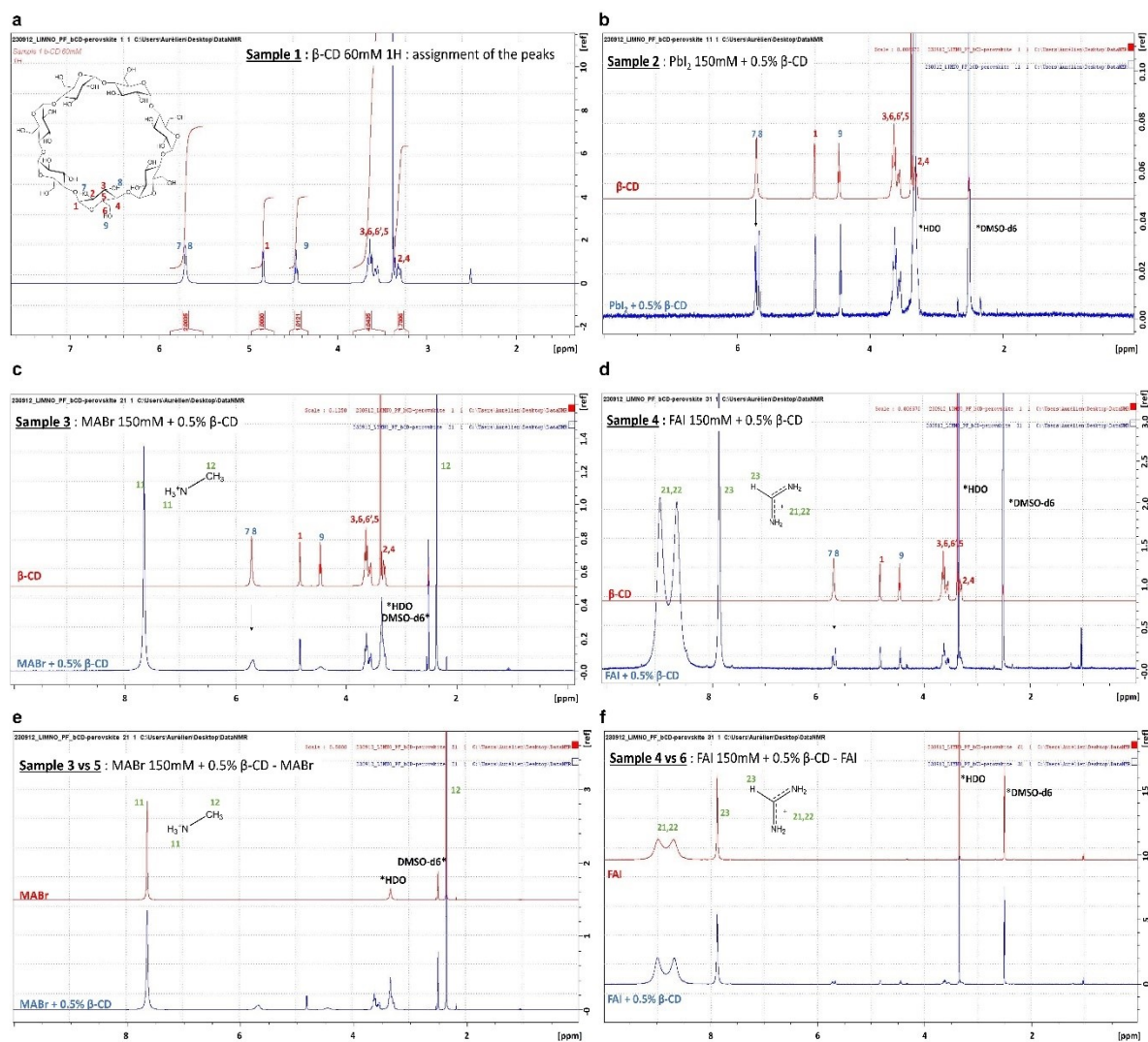
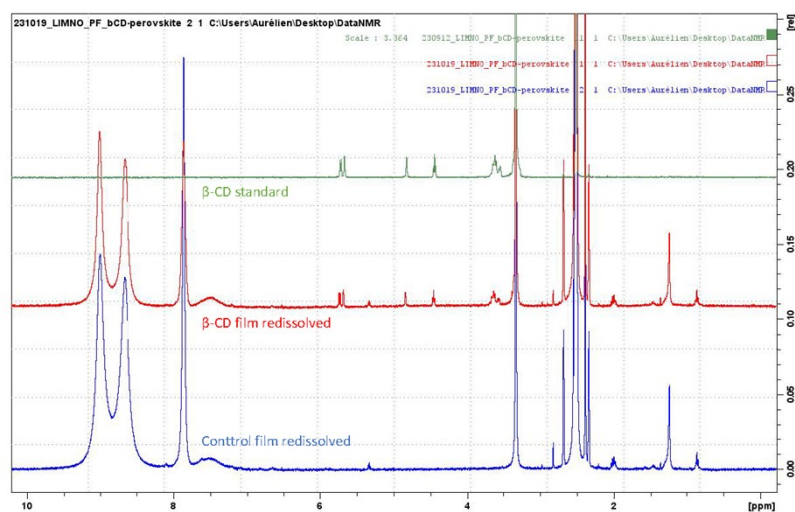


Figure S7. Solution ^1H NMR of a) β -CD, b) PbI_2 + 0.5% β -CD, c) MABr + 0.5% β -CD, d) FAI + 0.5% β -CD, e) MABr + 0.5% β -CD-MABr, and f) FAI + 0.5% β -CD-FAI precursor solutions in DMSO-d_6 .



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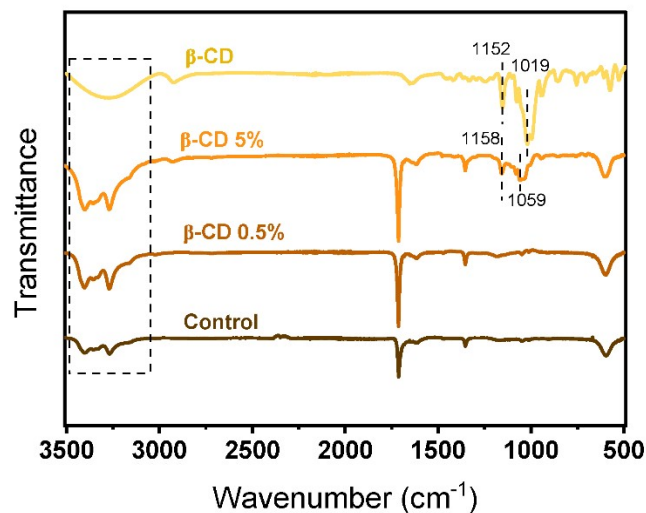


Figure S9. ATR-FTIR spectra of pure β -CD as powder, perovskite films without β -CD (control), and perovskite films treated by with 0.5% of β -CD and 5% of β -CD.

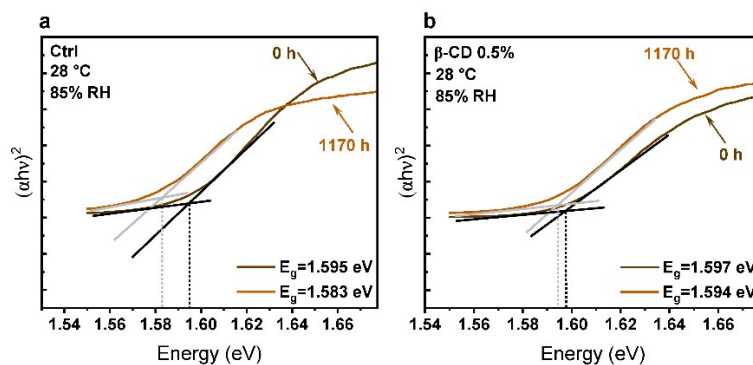


Figure S10. Plot of $(\alpha h\nu)^2$ as a function of photon energy for a) control and b) treated sample by 0.5% of β -CD before and after exposure to humidity stress.

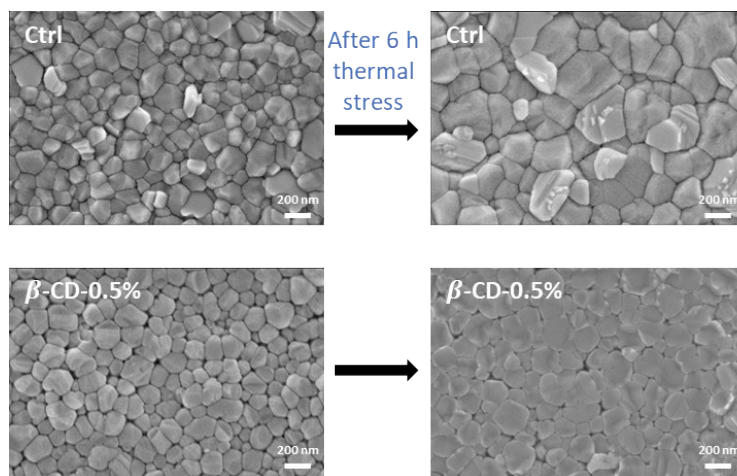


Figure S11. Top view SEM images of the control and β -CD 0.5% treated perovskite films before and after 6 hours aggressive thermal stress.

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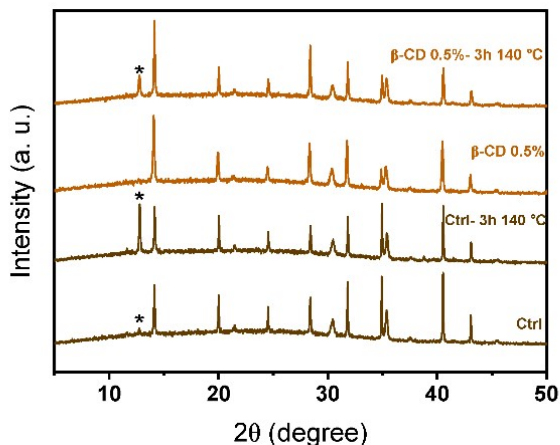


Figure S12. XRD pattern of control (ctrl) and treated sample by 0.5% of β -CD on ITO substrates covered by a SAM layer (star marks the XRD peak of PbI_2).

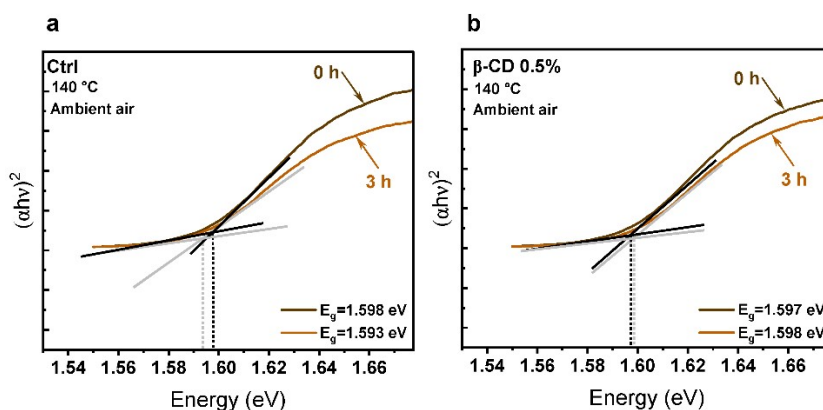


Figure S13. Plot of $(\alpha h\nu)^2$ as a function of photon energy for a) control and b) treated sample by 0.5% of β -CD before and after exposure to aggressive thermal stress.

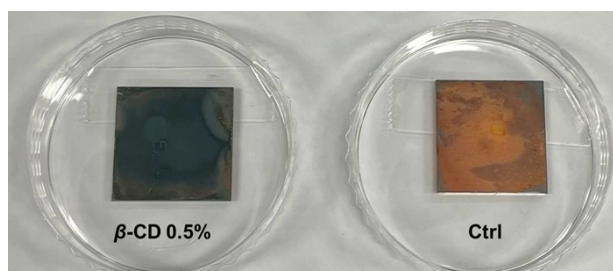


Figure S14. Images of control (ctrl) and treated sample by 0.5% of β -CD on ITO substrates after 5 months at a controlled environment with a temperature range of 18-20°C and humidity between 40 to 45%.

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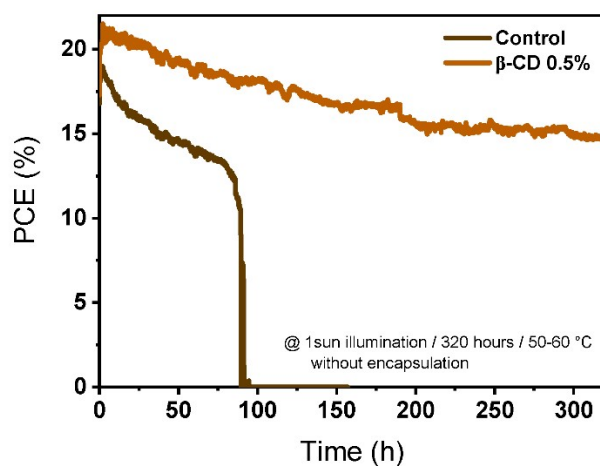


Figure S15. Long-term stability of control and β -CD 0.5% treated devices under constant 1-sun illumination without encapsulation, maintaining temperatures between 50 to 60°C.

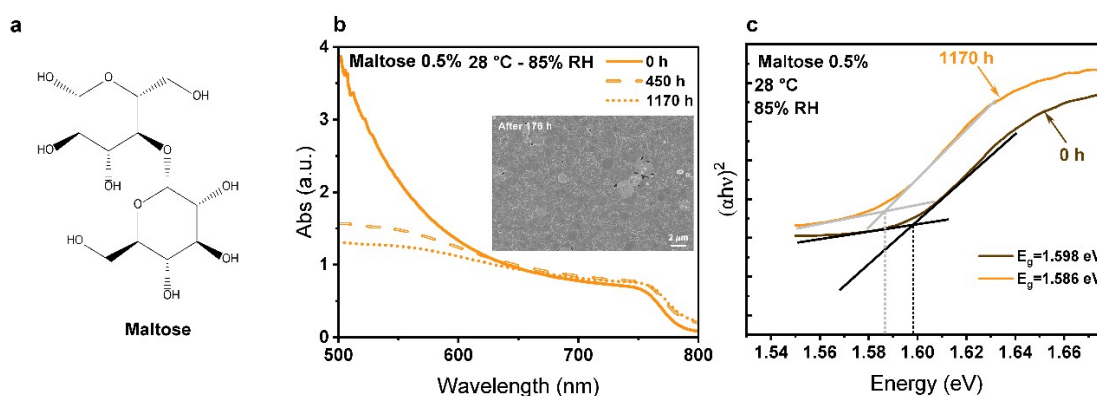


Figure S16. a) Chemical structure of Maltose and b) absorption spectra of Maltose 0.5% treated films under humidity environment (85% RH) at 27°C. Then inset shows top-view SEM image of film after 176-hour humidity exposure. c) Plot of $(\alpha h\nu)^2$ as a function of photon energy.

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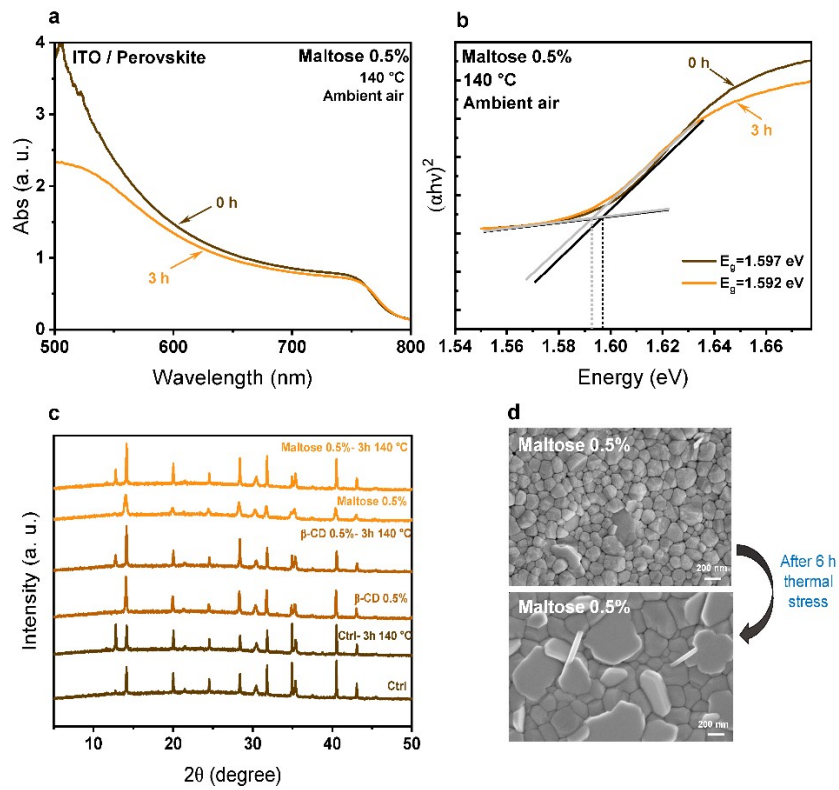


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Table S1. Average value of trap-filled limit voltage and trap-state density from SCLC.

Sample	Average $V_{TFL}(V)$	Average $N_{trap}(cm^{-3})$
β -CD 0.5%	0.353	1.14358E+16
Control	0.455	1.47193E+16